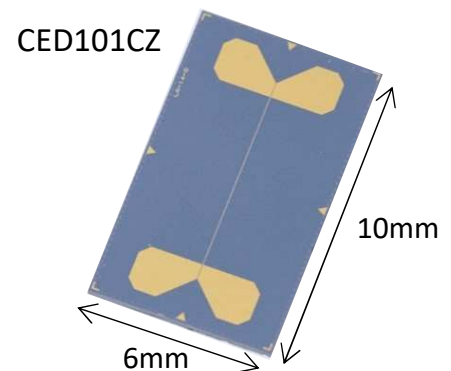
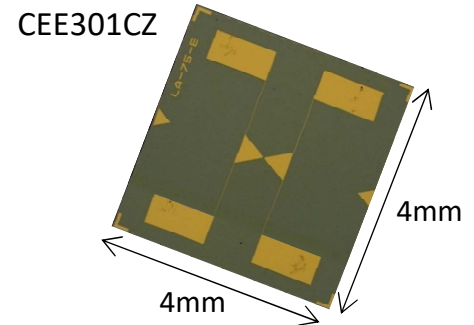


Experience unmatched performance with our **InGaAs PCA emitters** and **LT-GaAs PCA detectors**—precision-engineered to deliver **high dynamic range** and **broadband THz-TDS measurements**, optimized for use with **1.55 μm telecom-wavelength femtosecond lasers**. Available in **free-space PCA module** and **epi-wafer substrate** of InGaAs and LT-GaAs formats, these versatile components are ready to integrate into your advanced terahertz systems.

Structure

Model	CEE301CZ	CED101CZ
PCA type	Emitter	Detector
Chip size	4mm x 4mm	6mm x 10mm
Chip thickness	350 μm	350 μm
Antenna type	Bowtie	Dipole
Antenna gap	30 μm	3.4 μm
Substrate	InP	SI-GaAs
Photoconductive layer	Fe-doped InGaAs	LT-GaAs
Excitation wavelength	1560nm	780nm/1560nm



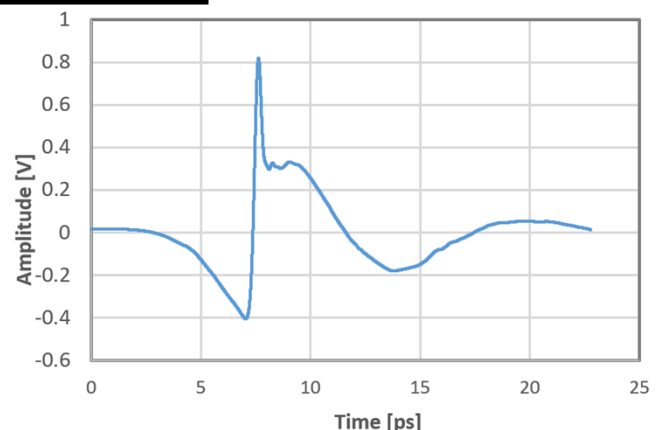
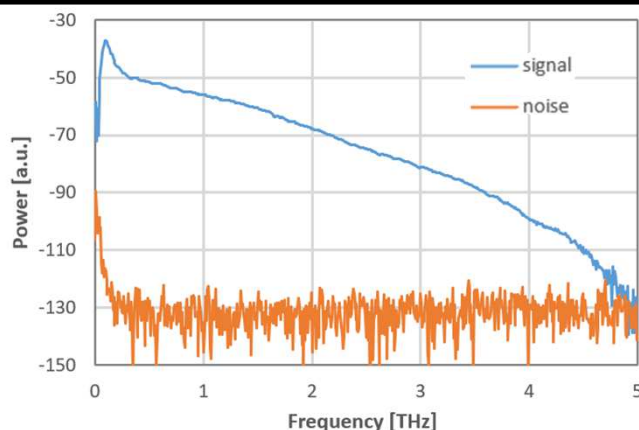
Absolute maximum ratings

Model	CEE301CZ	CED101CZ
Applied Voltage	$\pm 20\text{V}$	-
Average input optical Power ※1, ※2	20mW ※3	20mW
Operating temperature ※4	0°C to +40°C	0°C to +40°C
Storage temperature ※4	-20°C to +60°C	-20°C to +60°C

- ※1 Repetition rate from 50MHz to 150 MHz
- ※2 Pulse width larger than 30fs
- ※3 The beam diameter on the chip surface should be larger than 100 μm (1/e²)
- ※4 No condensation

Characteristics

Parameter	CEE301CZ	CED101CZ
Dark resistance (Minimum)	50k Ω	20M Ω



Note : This document may be changed without prior notice. Please check the latest document for examination.

April. 16, 2025 PI1898-1E

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